



BDY26 – 183T2
BDY27 – 184T2
BDY28 – 185T2

NPN SILICON TRANSISTORS, DIFFUSED MESA.

They are NPN transistors mounted in Jedec TO-3.
 LF Large Signal Power Amplification.
 High Current Fast Switching.
 Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
V_{CEO}	Collector-Emitter Voltage	BDY26, 183T2	180
		BDY27, 184T2	200
		BDY28, 185T2	250
V_{CBO}	Collector-Base Voltage	BDY26, 183T2	300
		BDY27, 184T2	400
		BDY28, 185T2	500
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current	6	A
I_B	Base Current	3	A
P_{TOT}	Power Dissipation @ $T_C = 25^\circ$	87.5	W
T_J	Junction Temperature	200	°C
T_S	Storage Temperature	-65 to +200	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	MAx	Unit	
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=50\text{ mA}$ $I_B=0$	BDY26, 183T2	180	-	-	V
			BDY27, 184T2	200	-	-	
			BDY28A, 185T2A	250	-	-	
			BDY28B, 185T2B	250	-	-	
			BDY28C, 185T2C	220	-	-	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (*)	$I_C=3\text{ mA}$	BDY26, 183T2	300	-	-	V
			BDY27, 184T2	400	-	-	
			BDY28, 185T2	500	-	-	
I_{CEO}	Collector-Emitter Cutoff Current	$V_{CE}=180\text{ V}$	BDY26	-	-	1.0	mA
		$V_{CE}=200\text{ V}$	BDY27	-	-		
		$V_{CE}=250\text{ V}$	BDY28	-	-		
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB}=10\text{ V}$	BDY26, 183T2 BDY27, 184T2 BDY28, 185T2	-	-	1.0	mA
I_{CES}	Collector-Emitter Cutoff Current	$V_{CE}=250\text{ V}$ $V_{BE}=0\text{ V}$	BDY26, 183T2	-	-	1.0	mA
		$V_{CE}=300\text{ V}$ $V_{BE}=0\text{ V}$	BDY27, 184T2	-	-		
		$V_{CE}=400\text{ V}$ $V_{BE}=0\text{ V}$	BDY28, 185T2	-	-		
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=2.0\text{ A}$ $I_B=0.25\text{ A}$	BDY26, 183T2	-	-	0.6	V
			BDY27, 184T2	-	-		
			BDY28, 185T2	-	-		
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	$I_C=2.0\text{ A}$ $I_B=0.25\text{ A}$	BDY26, 183T2	-	-	1.2	V
			BDY27, 184T2	-	-		
			BDY28, 185T2	-	-		
h_{FE}	DC Current Gain	$V_{CE}=4\text{ V}$ $I_C=1\text{ A}$	A	-	55	-	-
			B	-	65	-	
			C	-	90	-	
		$V_{CE}=4\text{ V}$ $I_C=2\text{ A}$	A	15	20	45	
			B	30	45	90	
			C	75	82	180	
f_T	Transition Frequency	$V_{CE}=15\text{ V}$, $I_C=0.5\text{ A}$, $f=10\text{ MHz}$	10	-	-	MHz	
$t_d + t_r$	Turn-on time	$I_C=5\text{ A}$, $I_B=1\text{ A}$	-	0.3	0.5	μs	
$t_s + t_f$	Turn-off time	$I_C=5\text{ A}$, $I_{B1}=1\text{ A}$, $I_{B2}=-0.5\text{ A}$	-	1.5	2.0	μs	

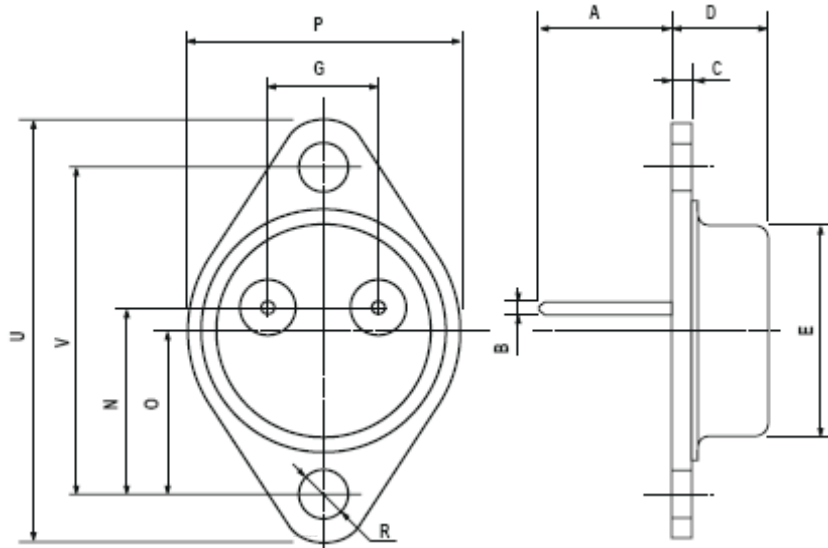
 (*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\angle 2\%$



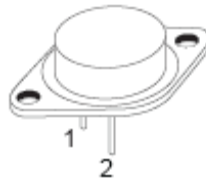
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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